## In the Claims

Claims 1-30 (Canceled).

- 31. (Currently amended) An engagement probe comprising:
- a substrate comprising bulk semiconductive material;
- a projection supported over the substrate and comprising material of the substrate;

and

- a grouping of a plurality of projecting apexes extending from the projection; and wherein the apexes are in the shape of multiple knife-edge lines, the multiple knife-edge lines being positioned to form at least one polygon.
- 32. (Previously presented) The engagement probe of claim 31 comprising a plurality of such groupings for engaging multiple conductive pads.

Claims 33-34 (Canceled).

35. (Currently amended) The engagement probe of claim 31 wherein the apexes are in the shape of multiple knife edge lines, the multiple knife-edge lines being are positioned to form at least two polygons, one of which is received entirely within the other.

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36. (Previously Presented) The engagement probe of claim 31 wherein the

grouping of apexes is formed on the projection which is supported by another projection,

the another projection extending directly from the substrate.

37. (Previously Presented) The engagement probe of claim 31 wherein the apexes

have a selected projecting distance, the projecting distance being about one-half the

thickness of the conductive pad which the apparatus is adapted to engage.

38. (Previously Presented) The engagement probe of claim 31 wherein the apexes

project from a common plane of the projection, the apexes having respective tips and

bases, the bases of adjacent projecting apexes being spaced from one another to define a

penetration stop plane therebetween.

39. (Previously Presented) The engagement probe of claim 31 wherein the apexes

project from a common plane of the projection, the apexes having respective tips and

bases, the bases of adjacent projecting apexes being spaced from one another to define a

penetration stop plane therebetween, the tips being a distance from the penetration stop

plane of about one-half the thickness of the conductive pad which the apparatus is

adapted to engage.

Claim 40 (Canceled).

- 41. (Previously Presented) The engagement probe of claim 31 wherein outermost portions of the electrically conductive apexes constitute a first electrically conductive material, and wherein the conductive pads for which the probe is adapted have outermost portions constituting a second electrically conductive material; the first and second electrically conductive materials being different.
- 42. (Previously Presented) An engagement probe formed from a semiconductor material and having a grouping of a plurality of projecting apexes positioned in sufficient proximity to one another to collectively engage a single conductive pad on a semiconductor substrate; and

wherein the apexes are in the shape of multiple knife-edge lines, the multiple knife-edge lines being positioned to form at least one polygon.

43. (Previously Presented) An engagement probe formed from a semiconductor material and having a grouping of a plurality of projecting apexes positioned in sufficient proximity to one another to collectively engage a single conductive pad on a semiconductor substrate; and

wherein the apexes are in the shape of multiple knife-edge lines, the multiple knife-edge lines being positioned to form at least two polygons one of which is received entirely within the other.

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44. (Previously Presented) An engagement probe formed from a semiconductor

material and having a grouping of a plurality of projecting apexes positioned in sufficient

proximity to one another to collectively engage a single conductive pad on a

semiconductor substrate; and

wherein the apexes are in the shape of multiple knife-edge lines, the multiple

knife-edge lines interconnecting to form at least one fully enclosed polygon.

45. (Previously Presented) The engagement probe of claim 31 wherein the plurality

of the projecting apexes extend from a substantially planar uppermost surface of the

projection.

46. (Previously Presented) The engagement probe of claim 31 wherein an entirety

of the projection is spaced from the substrate.

Claim 47-48 (Canceled).

49. (Previously Presented) An engagement probe comprising:

a substrate;

a projection supported over the substrate and comprising material of the substrate;

a grouping of a plurality of projecting apexes extending from the projection and

positioned in sufficient proximity to one another to collectively engage a single conductive

pad on a semiconductor substrate; and

wherein the apexes are in the shape of multiple knife-edge lines, the multiple

knife-edge lines being positioned to form at least two polygons one of which is received

entirely within the other.

50. (Previously presented) An engagement probe comprising:

a substrate;

a projection supported over a side of the substrate and comprising material of the

substrate;

a grouping of a plurality of projecting apexes extending from the projection and

positioned in sufficient proximity to one another to collectively engage a single conductive

pad on a semiconductor substrate; and

wherein the grouping of apexes is formed on the projection which is supported by

another projection, the another projection extending directly from the side of the substrate.

Claim 51 (Canceled).

52. (Previously presented) An engagement probe comprising:

a substrate;

a first projection supported over the substrate and comprising material of the

substrate;

a second projection over the first projection and comprising material of the

substrate;

a grouping of a plurality of projecting apexes extending from the second projection

and positioned in sufficient proximity to one another to collectively engage a single

conductive pad on a semiconductor substrate; and

wherein the apexes project from a common plane of the second projection, the

apexes having respective tips and bases, the bases of adjacent projecting apexes being

spaced from one another to define a penetration stop plane therebetween, the tips being a

distance from the penetration stop plane of about one-half the thickness of the conductive

pad which the apparatus is adapted to engage.

Claims 53-54 (Canceled).

55. (Previously Presented) The engagement probe of claim 31 further comprising

an intermediate structure between the projection and the substrate, wherein the

intermediate structure comprises a lateral dimension that is different from a lateral

dimension of the substrate and a lateral dimension of the projection.

Claims 56-59 (Canceled).

- (Previously presented) The engagement probe of claim 31 wherein the projection comprises a lateral dimension less than a lateral dimension of the substrate.
- (Previously presented) The engagement probe of claim 31 wherein the 61. substrate comprises a wafer.
- 62. (Previously presented) The engagement probe of claim 31 wherein the bulk semiconductive material comprises bulk silicon.
  - 63. (Previously presented) An engagement probe comprising:

a substrate;

a projection supported over the substrate and comprising material of the substrate;

a grouping of a plurality of projecting apexes extending from the projection and positioned in sufficient proximity to one another to collectively engage a single conductive pad on a semiconductor substrate;

wherein the projection comprises a lateral dimension less than a lateral dimension of the substrate; and

wherein the apexes are in the shape of multiple knife-edge lines, the multiple knife-edge lines being positioned to form at least one polygon.

64. (Previously presented) The engagement probe of claim 63 wherein the apexes are positioned to form at least two polygons one of which is received entirely within the other.

- 65. (Previously presented) The engagement probe of claim 63 wherein the apexes are positioned to form the multiple knife-edge lines interconnecting to form at least one fully enclosed polygon.
- 66. (Previously presented) The engagement probe of claim 31 wherein the material of the projection is the bulk semiconductive material.
- 67. (Previously presented) The engagement probe of claim 66 wherein the material of the plurality of the projecting apexes is the bulk semiconductive material.

Claims 68-74 (Canceled).

75. (New) An engagement probe comprising:

a substrate comprising bulk semiconductive material;

a projection supported over the substrate and comprising material of the substrate;

a grouping of a plurality of projecting apexes extending from the projection; and

wherein the apexes are in the shape of multiple knife-edge lines, the multiple

knife-edge lines interconnecting to form at least one fully enclosed polygon.